

<b>SILICON BRIDGE RECTIFIERS</b>	<p style="text-align: right;"> <b>REVERSE VOLTAGE - 50 to 1000Volts</b>  <b>FORWARD CURRENT - 6.0 Amperes</b> </p> <div style="text-align: center; margin: 10px 0;"> <b>KBJ</b> </div> <p style="text-align: center;">Dimensions in inches and (millimeters)</p>
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## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	KBJ6005	KBJ601	KBJ602	KBJ604	KBJ606	KBJ608	KBJ610	UNIT	
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V	
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V	
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V	
Maximum Average Forward Rectified Current @ T <sub>c</sub> =100°C (without heatsink)	I <sub>(AV)</sub>					6.0				A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>					175				A
Maximum Forward Voltage at 3.0A DC	V <sub>F</sub>					1.0				V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I <sub>R</sub>					10				μA
I <sup>2</sup> t Rating for Fusing (t<8.3ms)	I <sup>2</sup> t					120				A <sup>2</sup> s
Typical Junction Capacitance Per Element (Note1)	C <sub>J</sub>					55				pF
Typical Thermal Resistance (Note2)	R <sub>θJC</sub>					1.8				°C/W
Operating Temperature Range	T <sub>J</sub>					-55 to +125				°C
Storage Temperature Range	T <sub>STG</sub>					-55 to +150				°C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Device mounted on 75mm\*75mm\*1.6mm cu plate heatsink.



FIG.1-FORWARD CURRENT DERATING CURVE

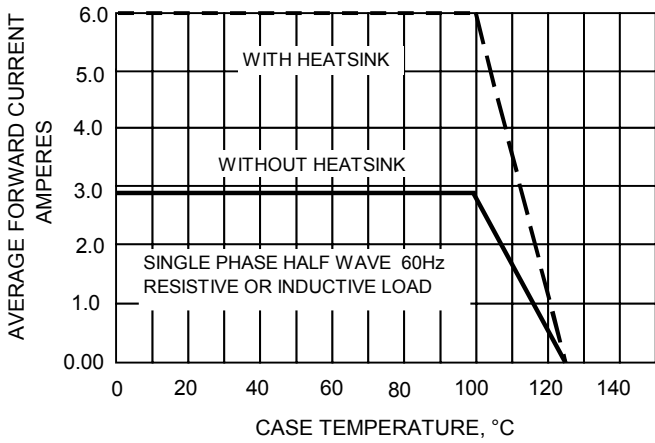


FIG.2-MAXIMUM NON-REPETITIVE SURGE CURRENT

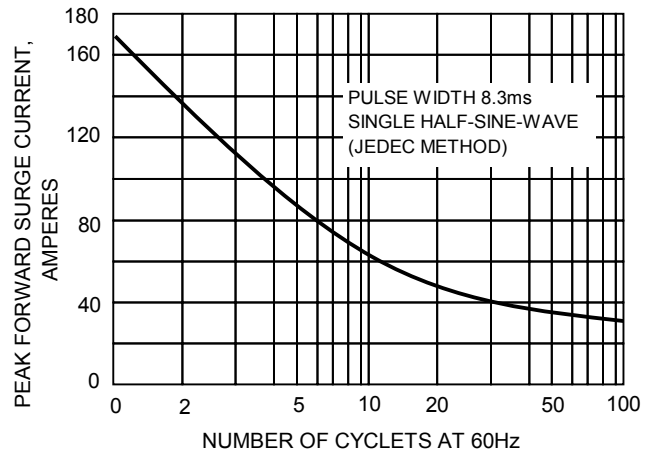


FIG.3-TYPICAL JUNCTION CAPACITANCE

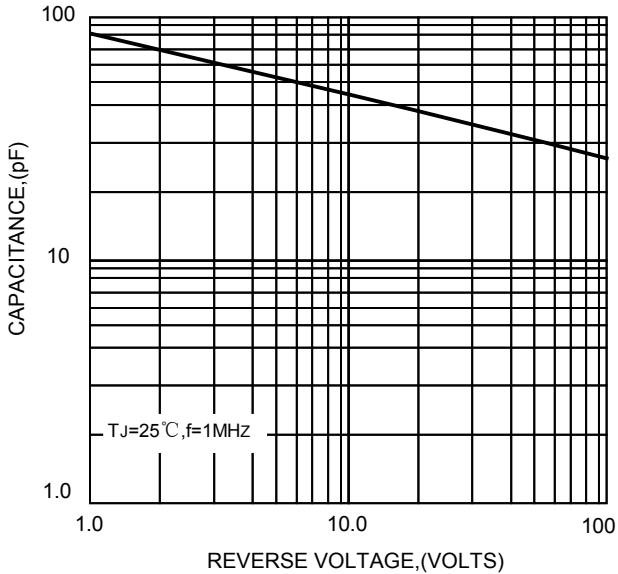


FIG.4-TYPICAL FORWARD CHARACTERISTICS

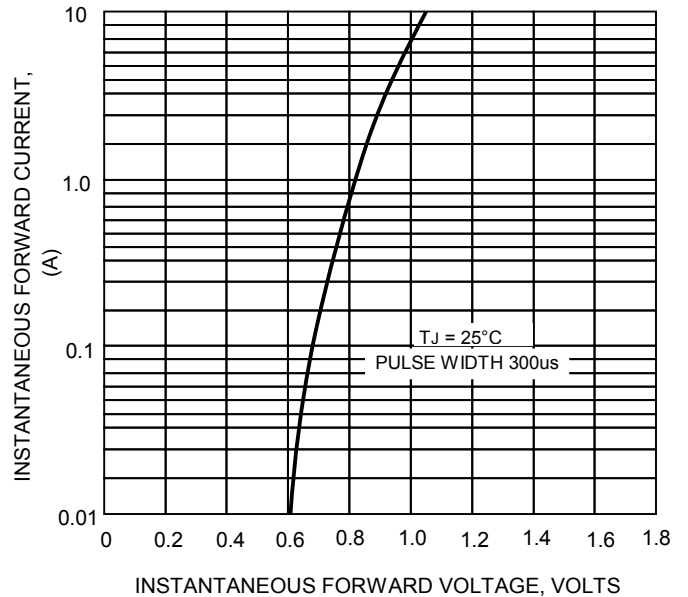


FIG.5-TYPICAL REVERSE CHARACTERISTICS

